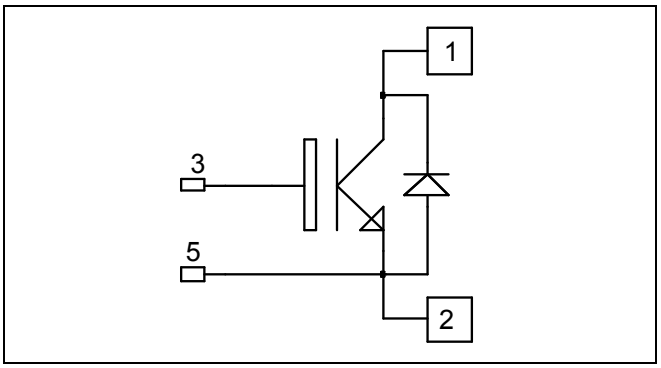
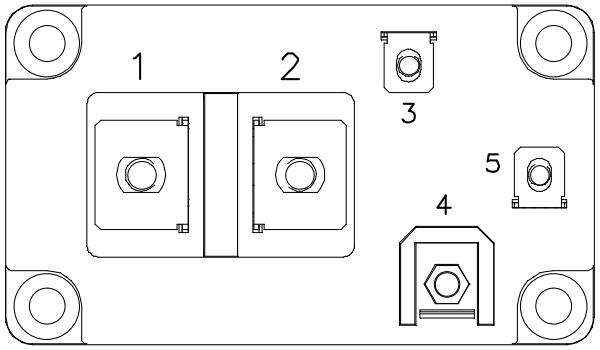
Single switch NPT IGBT Power Module

V_{CES} = 600V
I_C = 360A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	450	A
		T_C = 80°C	360	
I_{CM}	Pulsed Collector Current	T_C = 25°C	720	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	1560	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	800A@520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 600V	T_j = 25°C			500	µA
			T_j = 125°C			1	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V I_C = 400A	T_j = 25°C		1.95	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, I_C = 6mA		4.5	5.5	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				1200	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz			17		nF
C_{res}	Reverse Transfer Capacitance				1.6		
Q_G	Gate charge	V_{GE}=15V, I_C=400A V_{CE}=300V			1		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 400A R_G = 8Ω			150		ns
T_r	Rise Time				72		
$T_{d(off)}$	Turn-off Delay Time				530		
T_f	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 400A R_G = 8Ω			160		ns
T_r	Rise Time				75		
$T_{d(off)}$	Turn-off Delay Time				550		
T_f	Fall Time				50		
E_{on}	Turn on Energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 400A R_G = 8Ω	T_j = 125°C		18.6		mJ
E_{off}	Turn off Energy		T_j = 125°C		17.3		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq$15V ; V_{Bus} = 360V $t_p \leq$ 10µs ; T_j = 125°C			1800		A

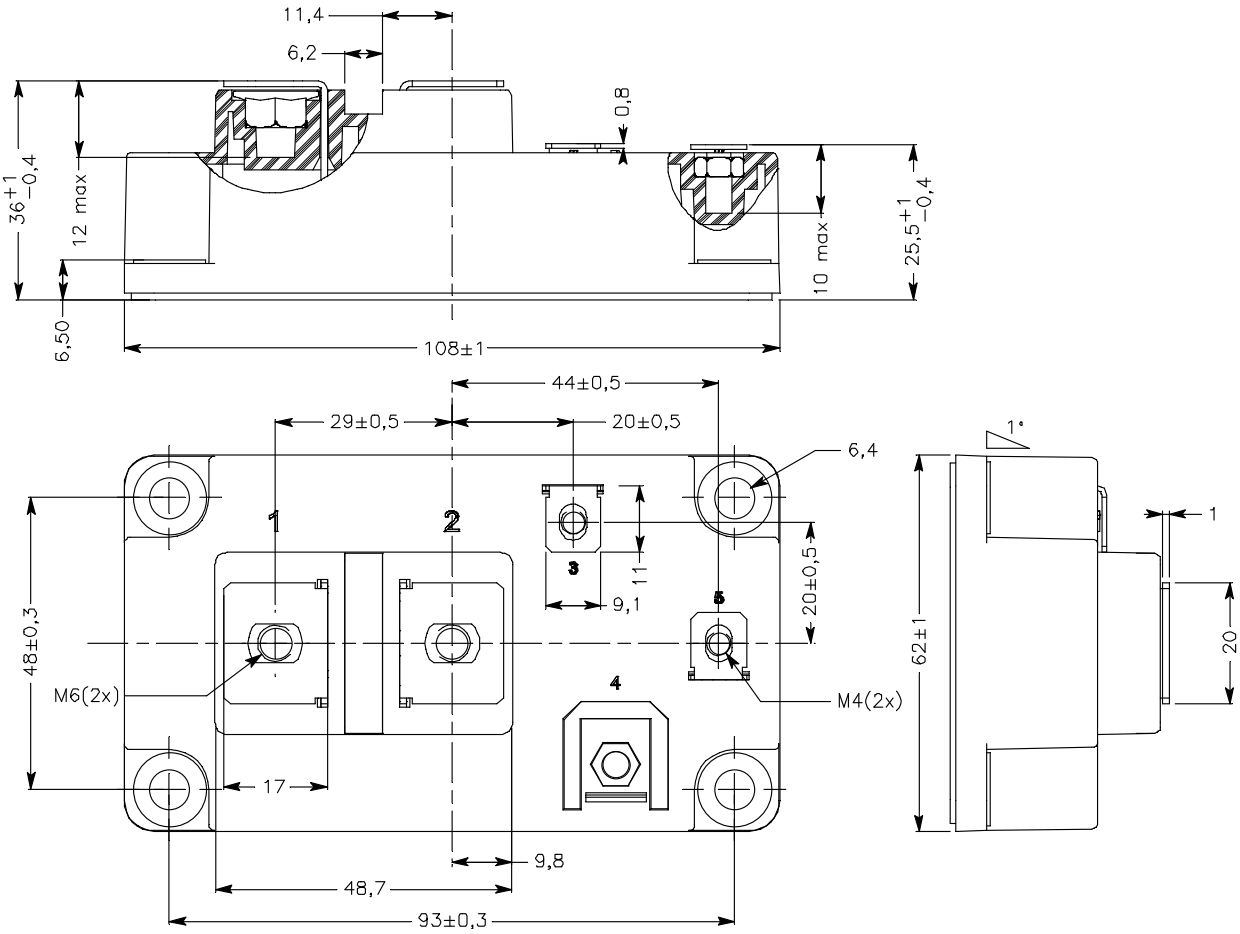
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RRM}	Maximum Reverse Leakage Current	V_R = 600V	T_j = 25°C			750	µA
			T_j = 125°C			1000	
I_F	DC Forward Current		Tc = 80°C		400		A
V_F	Diode Forward Voltage	I_F = 400A V_{GE} = 0V	T_j = 25°C		1.25	1.6	V
			T_j = 125°C		1.2		
t_{rr}	Reverse Recovery Time	I_F = 400A V_R = 300V di/dt =4400A/µs	T_j = 25°C		150		ns
			T_j = 125°C		250		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		27		µC
			T_j = 125°C		44		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		5.6		mJ
			T_j = 125°C		9.2		

Thermal and package characteristics

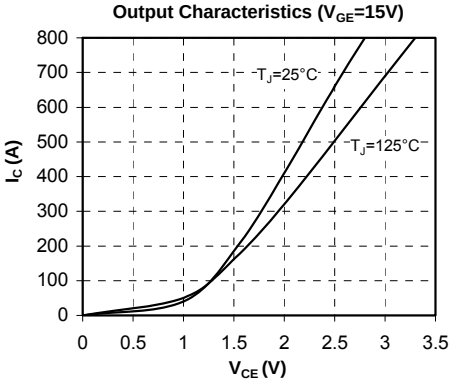
Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.08	°C/W
		Diode			0.15	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		125	
Torque	Mounting torque	M6	3		5	N.m
		M4	1		2	
Wt	Package Weight				350	g

D4 Package outline (dimensions in mm)

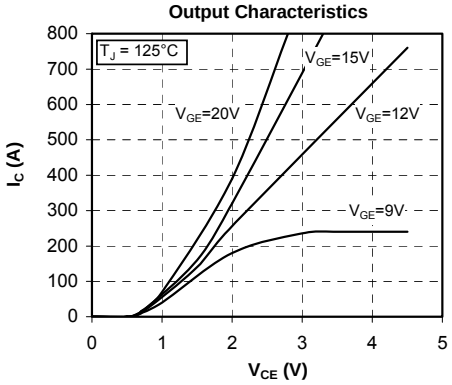


Typical Performance Curve

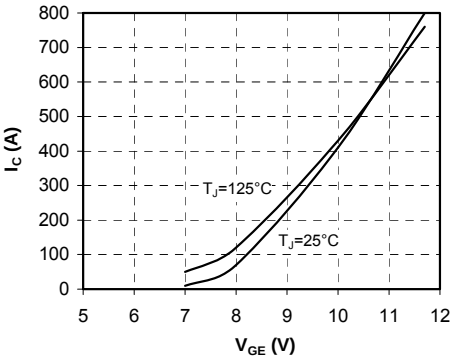
Output Characteristics (V_{GE}=15V)



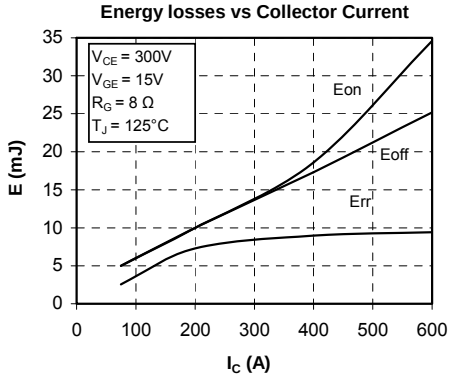
Output Characteristics



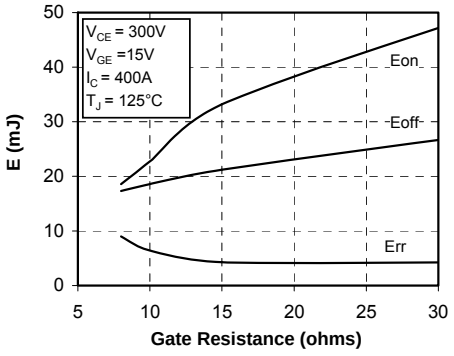
Transfert Characteristics



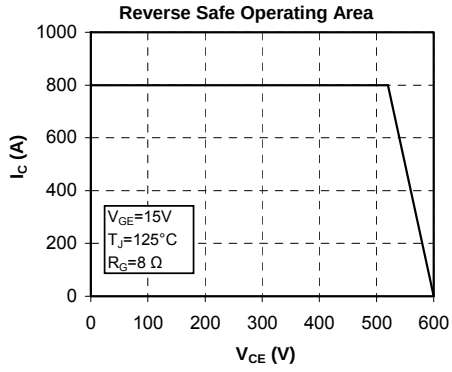
Energy losses vs Collector Current



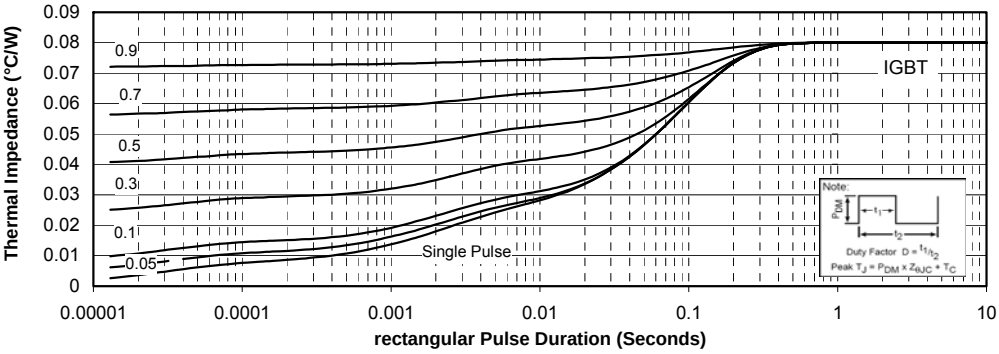
Switching Energy Losses vs Gate Resistance

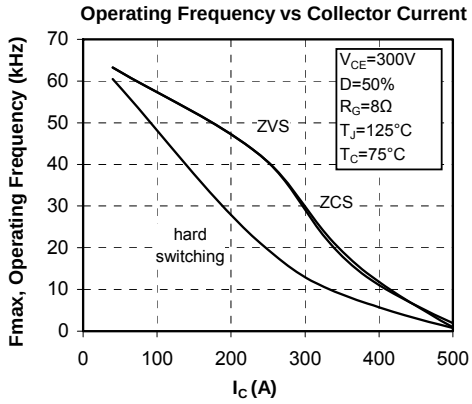


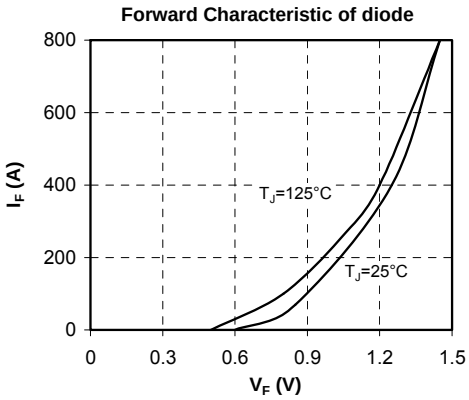
Reverse Safe Operating Area

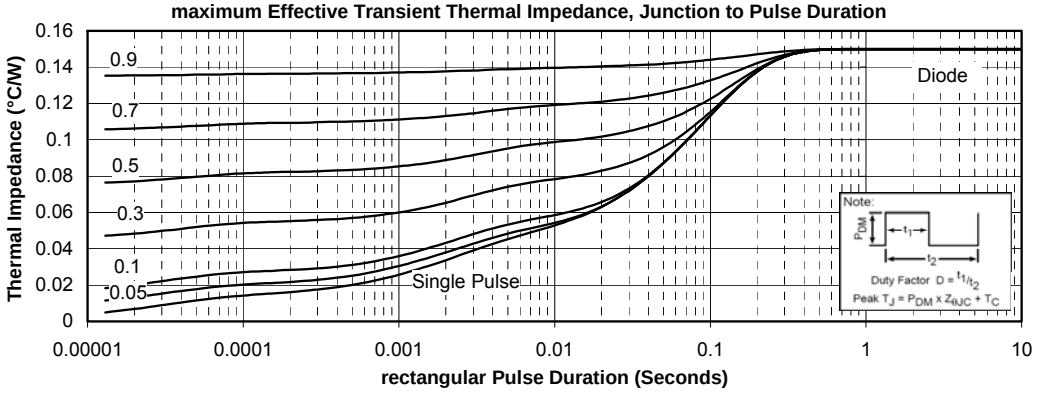


maximum Effective Transient Thermal Impedance, Junction to Pulse Duration









Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.